**Product data sheet** 

## 1. General description

Planar passivated high commutation three quadrant triac in a TO263 (D2PAK) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series C" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber.

#### 2. Features and benefits

- · 3Q technology for improved noise immunity
- · High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- · High voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only

### 3. Applications

- Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoid

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Absolute	maximum rating						
$V_{DRM}$	repetitive peak off-state voltage			-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	MS on-state current full sine wave; T <sub>mb</sub> ≤ 101 °C Fig. 1; Fig. 2; Fig. 3		-	-	16	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms Fig. 4; Fig. 5		-	-	140	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms		-	-	150	Α
T <sub>j</sub>	junction temperature			-	-	125	°C
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		2	-	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_i = 25 \text{ °C; } Fig. 7$		2	-	35	mA

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$		2	-	35	mA	
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>		-	-	35	mA	
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 18 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>		-	1.3	1.5	V	
Dynamic	characteristics							
dV <sub>D</sub> /dt	rate of rise of off-stat voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit		500	-	-	V/µs	
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$		15	-	-	A/ms	

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		T2——T1
3	G	gate		K G
mb	T2	mounting base; main terminal 2		sym051

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA316B-800C	TO263	BTA316B-800C,118	Reel	800	TO263E (E)	26-May-2017
					TO263P (P)	12-Jun-2023

## 7. Marking

#### **Table 4. Marking codes**

Type number	Marking codes		
	Assembly factory: E	Assembly factory: P	
BTA316B-800C	BTA316B 800C	BTA316B 800C	
	PJExxxx xx	PJPxxxx xx	

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 101 °C Fig 1; Fig 2; Fig 3	-	16	А
I <sub>TSM</sub> non-repetitive peak on- state current		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms Fig 4; Fig 5	-	140	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	150	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN	-	98	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 70 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

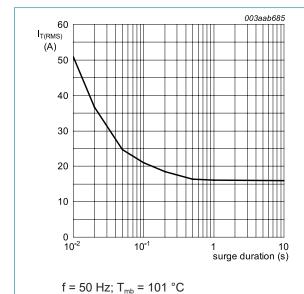


Fig. 1. RMS on-state current as a function of surge duration; maximum values

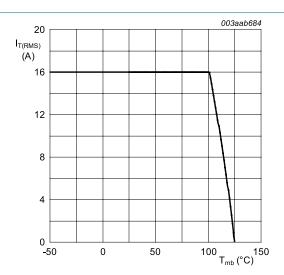
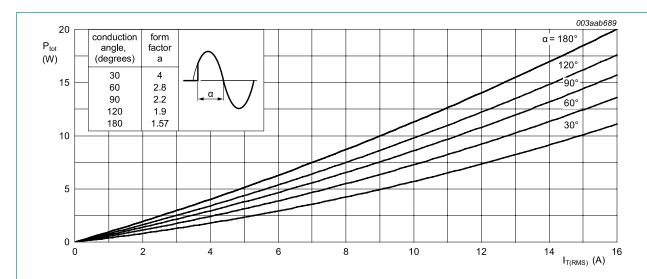


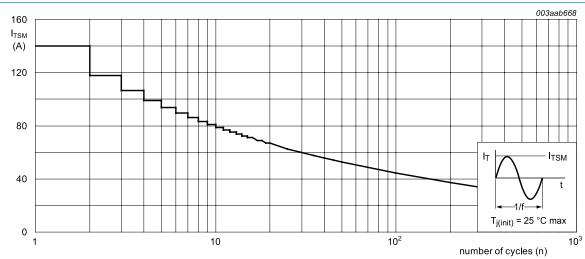
Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



 $\alpha$  = conduction angle

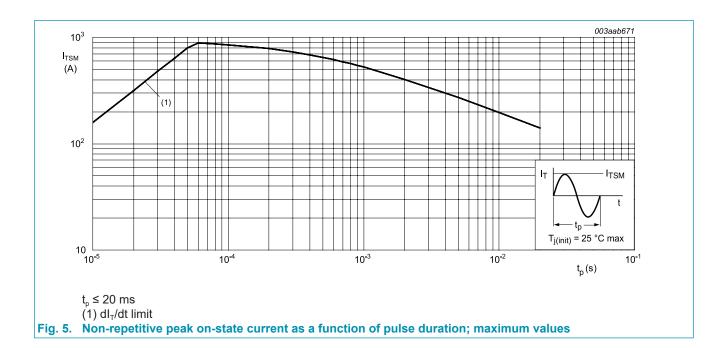
 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub> thermal resistance		full cycle; Fig 6	-	-	1.2	K/W
	from junction to mounting base	half cycle; Fig 6	-	-	1.7	K/W
R <sub>th(j-a)</sub>			-	55	-	K/W

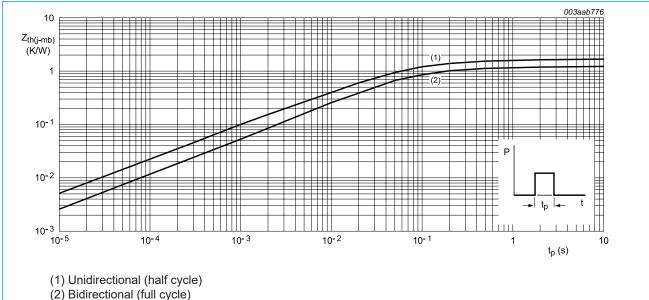
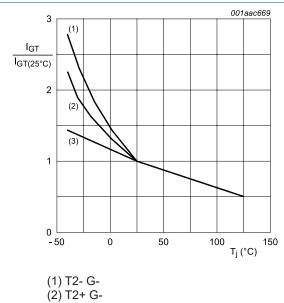


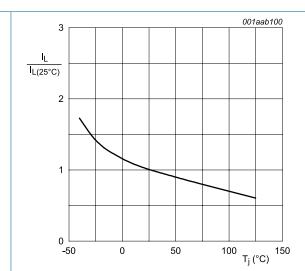
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	2	-	35	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	50	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	35	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 18 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.8	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state curren	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics		'			
dV <sub>D</sub> /dt	rate of rise of off-stat voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 16 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit	15	-	-	A/ms

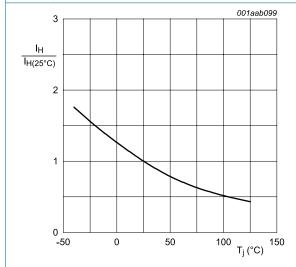


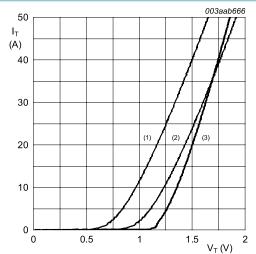


(3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature



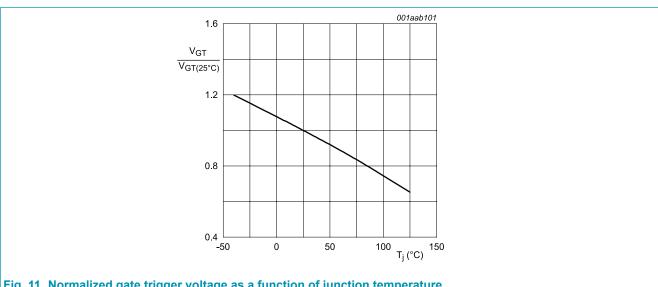


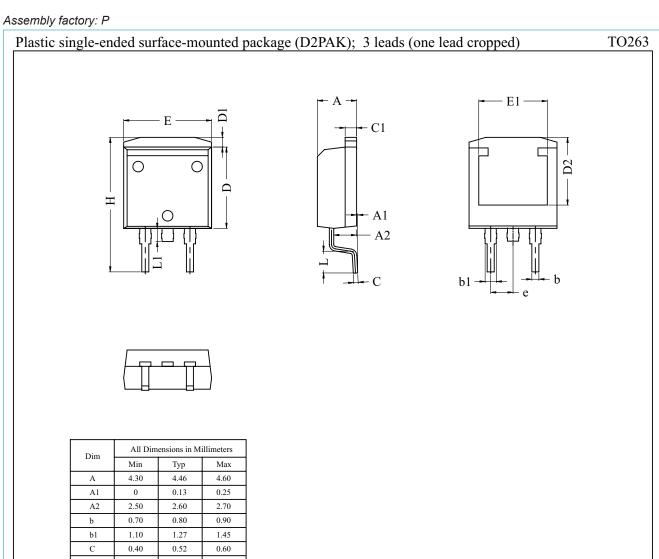


- $V_o$  = 1.024 V;  $R_s$  = 0.021 Ω (1)  $T_j$  = 125 °C; typical values
- (2)  $T_i = 125$  °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

Fig. 9. Normalized holding current as a function of junction temperature

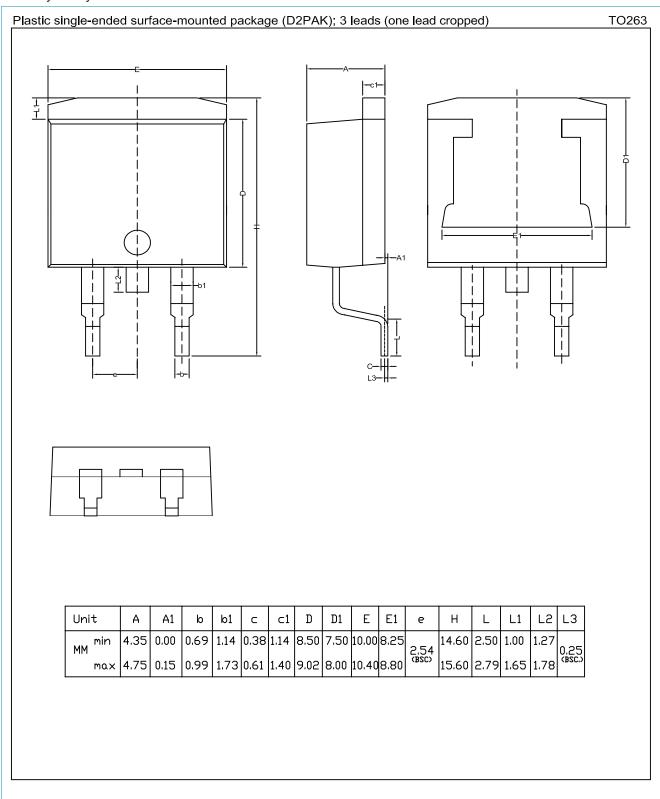
Fig. 10. On-state current as a function of on-state voltage





Dim	All Dimensions in Millimeters				
Diiii	Min	Тур	Max		
A	4.30	4.46	4.60		
A1	0	0.13	0.25		
A2	2.50	2.60	2.70		
b	0.70	0.80	0.90		
bl	1.10	1.27	1.45		
С	0.40	0.52	0.60		
C1	1.17	1.30	1.40		
D	9.10	9.25	9.40		
D1	1.00	1.10	1.30		
D2	7.40	7.70	8.00		
Е	9.80	10.00	10.20		
E1	7.60	7.80	8.00		
e	2.54 BSC				
Н	14.80	15.30	15.80		
L	2.10	2.47	2.80		
L1	1.30	1.50	1.70		

#### Assembly factory: E



### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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